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Low Voltage Quad 2-Input OR Gate with 5 V Tolerant Inputs

74LCX32

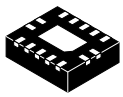
The LCX32 contains four 2−input OR gates. The inputs tolerate voltages up to 7 V allowing the interface of 5 V systems to 3 V systems.

The 74LCX32 is fabricated with advanced CMOS technology to achieve high speed operation while maintaining CMOS low power dissipation.

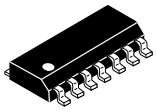
Features

- 5 V Tolerant Inputs
- 2.3 V – 3.6 V V_{CC} Specifications Provided
- 5.5 ns t_{PD} Max. (V_{CC} = 3.3 V), 10 mA I_{CC} Max.
- Power Down High Impedance Inputs and Outputs
- ±24 mA Output Drive (V_{CC} = 3.0 V)
- Implements Proprietary Noise/EMI Reduction Circuitry
- Latch−up Performance Exceeds JEDEC 78 Conditions
- ESD performance:
  - ♦ Human Body Model >2000 V
  - ♦ Machine model >150 V
- Available on SOIC, TSSOP WB and Leadless QFN Packages
- These are Pb−Free Devices

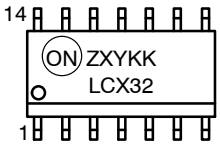
MARKING DIAGRAM

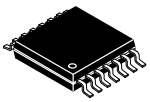


QFN14 3.0x2.5, 0.5P
CASE 510CB

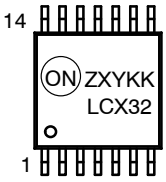


SOIC14
CASE 751EF





TSSOP−14 WB
CASE 948G



LCX32	= Specific Device Code
Z	= Assembly Plant Code
XY	= Date Code
KK	= Lot Run Traceability Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

CONNECTION DIAGRAMS

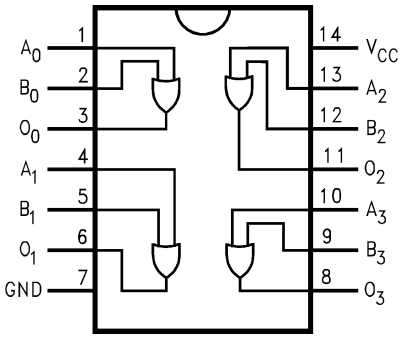


Figure 1. Pin Assignments for SOIC and TSSOP

LOGIC SYMBOL

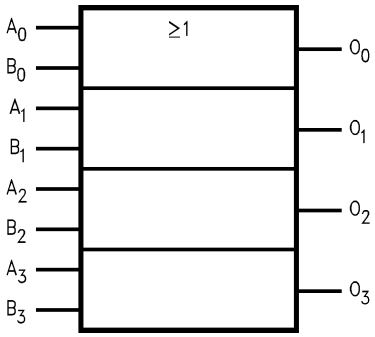
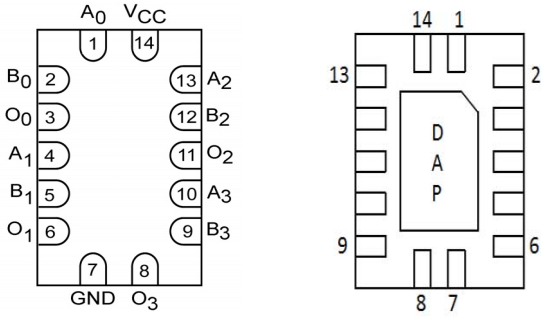


Figure 3. IEEE/IEC



(Top View) (Bottom View)

Figure 2. Pad Assignments for DQFN

PIN DESCRIPTION

Pin Names	Description
A_n, B_n	Inputs
O_n	Outputs
DAP	No Connect

1. DAP (Die Attach Pad)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Rating
V_{CC}	Supply Voltage	–0.5 V to +7.0 V
V_I	DC Input Voltage	–0.5 V to +7.0 V
V_O	DC Output Voltage, Output in HIGH or LOW State (Note 2)	–0.5 V to V_{CC} + 0.5 V
I_{IK}	DC Input Diode Current, V_I < GND	–50 mA
I_{OK}	DC Output Diode Current V_O < GND	–50 mA
	V_O > V_{CC}	+50 mA
I_O	DC Output Source/Sink Current	±50 mA
I_{CC}	DC Supply Current per Supply Pin	±100 mA
I_{GND}	DC Ground Current per Ground Pin	±100 mA
T_{STG}	Storage Temperature	–65°C to +150°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. I_O Absolute Maximum Rating must be observed.

RECOMMENDED OPERATING CONDITIONS (Note 3)

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply Voltage Operating	2.0	3.6	V
	Data Retention	1.5	3.6	
V_I	Input Voltage	0	5.5	V
V_O	Output Voltage, HIGH or LOW State	0	VCC	V
I_{OH} / I_{OL}	Output Current V_{CC} = 3.0 V – 3.6 V	–	±24	mA
	V_{CC} = 2.7 V – 3.0 V	–	±12	
	V_{CC} = 2.3 V – 2.7 V	–	±8	
T_A	Free–Air Operating Temperature	–40	85	°C
$\Delta t / \Delta V$	Input Edge Rate, V_{IN} = 0.8 V – 2.0 V, V_{CC} = 3.0 V	0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

3. Unused inputs must be held HIGH or LOW. They may not float.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	V_{CC} (V)	Conditions	–40°C to 85°C		Unit
				Min	Max	
V_{IH}	HIGH Level Input Voltage	2.3 – 2.7		1.7	–	V
		2.7 – 3.6		2.0	–	
V_{IL}	LOW Level Input Voltage	2.3 – 2.7		–	0.7	V
		2.7 – 3.6		–	0.8	
V_{OH}	HIGH Level Output Voltage	2.3 – 3.6	I_{OH} = –100 μA	V_{CC} – 0.2	–	V
		2.3	I_{OH} = –8 mA	1.8	–	
		2.7	I_{OH} = –12 mA	2.2	–	
		3.0	I_{OH} = –18 mA	2.4	–	
			I_{OH} = –24 mA	2.2	–	
V_{OL}	LOW Level Output Voltage	2.3 – 3.6	I_{OL} = 100 μA	–	0.2	V
		2.3	I_{OL} = 8 mA	–	0.6	
		2.7	I_{OL} = 12 mA	–	0.4	
		3.0	I_{OL} = 16 mA	–	0.4	
			I_{OL} = 24 mA	–	0.55	
I_I	Input Leakage Current	2.3 – 3.6	0 ≤ V_I ≤ 5.5 V	–	±5.0	μA
I_{OFF}	Power–Off Leakage Current	0	V_I or V_O = 5.5 V	–	10	μA
I_{CC}	Quiescent Supply Current	2.3 – 3.6	V_I = V_{CC} or GND	–	10	μA
			3.6 V ≤ V_I ≤ 5.5 V	–	±10	
ΔI_{CC}	Increase in I_{CC} per Input	2.3 – 3.6	V_{IH} = V_{CC} – 0.6 V	–	500	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	T_A = –40°C to +85°C, RL = 500 Ω						Unit
		V_{CC} = 3.3 V + 0.3 V, C_L = 50 pF		V_{CC} = 2.7 V, C_L = 50 pF		V_{CC} = 2.5 V + 0.2 V, C_L = 30 pF		
		Min	Max	Min	Max	Min	Max	
t_{PHL}, t_{PLH}	Propagation Delay	1.5	5.5	1.5	6.2	1.5	6.6	ns
t_{OSHL}, t_{OSLH}	Output to Output Skew (Note 4)	–	1.0	–	–	–	–	ns

4. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH−to−LOW (t_{OSHL}) or LOW−to−HIGH (t_{OSLH}).

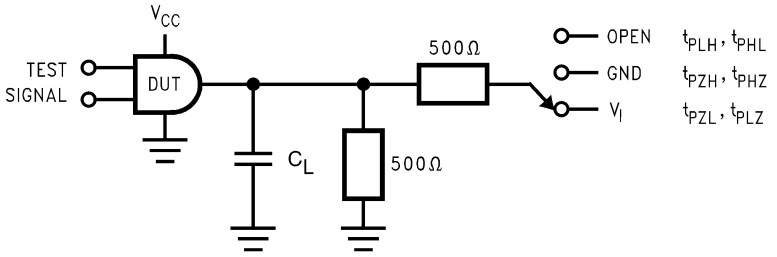
DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	V_{CC} (V)	Conditions	T_A = 25°C	Unit
				Typical	
V_{OLP}	Quiet Output Dynamic Peak V_{OL}	3.3	C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V	0.8	V
		2.5	C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V	0.6	
V_{OLV}	Quiet Output Dynamic Valley V_{OL}	3.3	C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V	–0.8	V
		2.5	C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V	–0.6	

CAPACITANCE

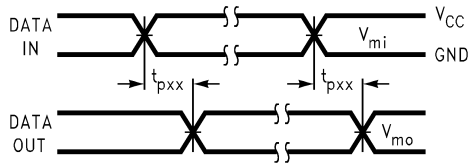
Symbol	Parameter	Conditions	Typical	
C_{IN}	Input Capacitance	V_{CC} = Open, V_I = 0 V or V_{CC}	7	pF
C_{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	8	pF
C_{PD}	Power Dissipation Capacitance	V_{CC} = 3. 3 V, V_I = 0 V or V_{CC}, f = 10 MHz	25	pF

AC LOADING AND WAVEFORMS (GENERIC FOR LCX FAMILY)

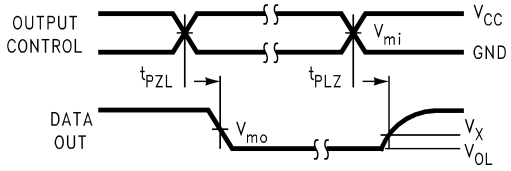


Test	Switch
t_{PLH}, t_{PHL}	Open
t_{PZL}, t_{PLZ}	6 V at V_{CC} = 3.3 ± 0.3 V V_{CC} x 2 at V_{CC} = 2.5 ± 0.2 V
t_{PZH}, t_{PHZ}	GND

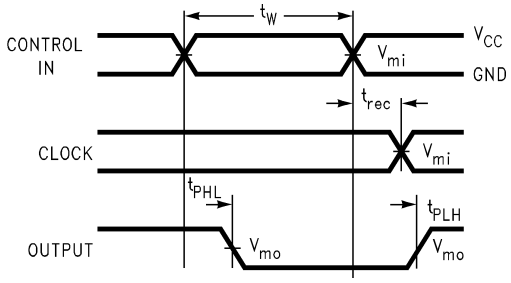
Figure 4. AC Test Circuit (C_L Includes Probe and Jig Capacitance)



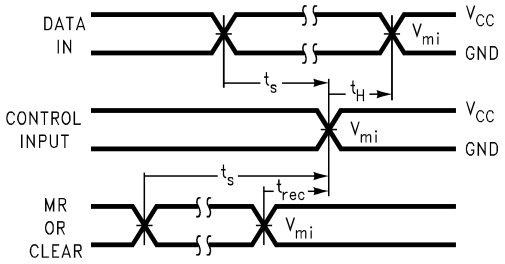
Waveform for Inverting and Non−Inverting Functions



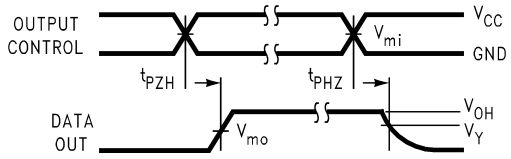
3−STATE Output Low Enable and Disable Times for Logic



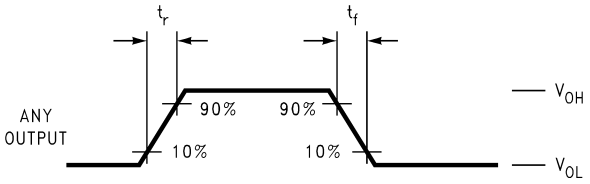
Propagation Delay. Pulse Width and trec Waveforms



Setup Time, Hold Time and Recovery Time for Logic



3−STATE Output High Enable and Disable Times for Logic



trise and tfall

Symbol	V_{CC}		
	3.3 V ± 0.3 V	2.7 V	2.5 V ± 0.2 V
V_{mi}	1.5 V	1.5 V	$_{CC}$ / 2
V_{mo}	1.5 V	1.5 V	$_{CC}$ / 2
V_x	V_{OL} + 0.3 V	V_{OL} + 0.3 V	V_{OL} + 0.15 V
V_y	V_{OH} − 0.3 V	V_{OH} − 0.3 V	V_{OH} − 0.15 V

Figure 5. Waveforms (Input Characteristics; f = 1 MHz, t_r = t_f = 3 ns)

SCHEMATIC DIAGRAM (GENERIC FOR LCX FAMILY)

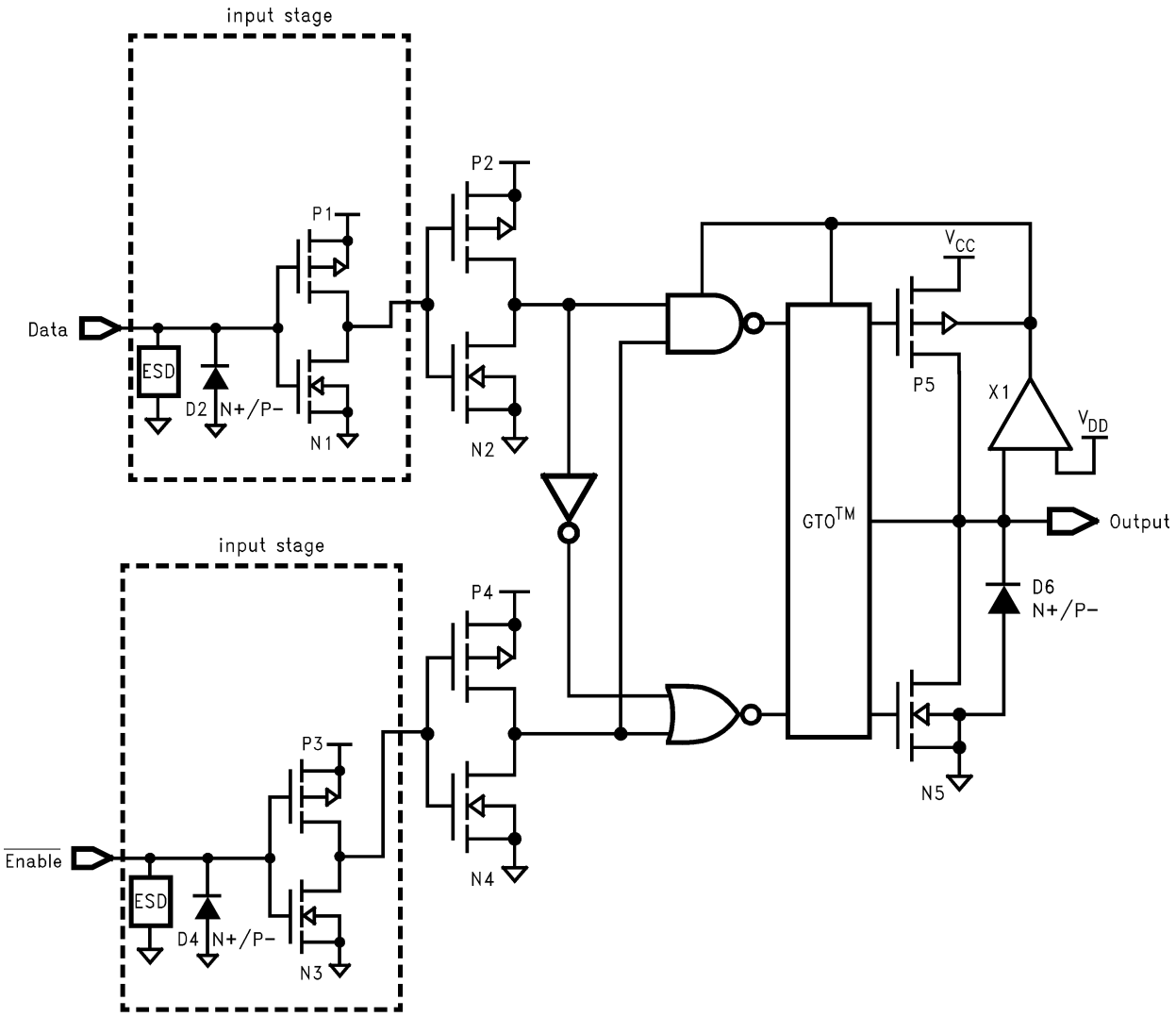


Figure 6. Schematic Diagram (Generic for LCX Family)

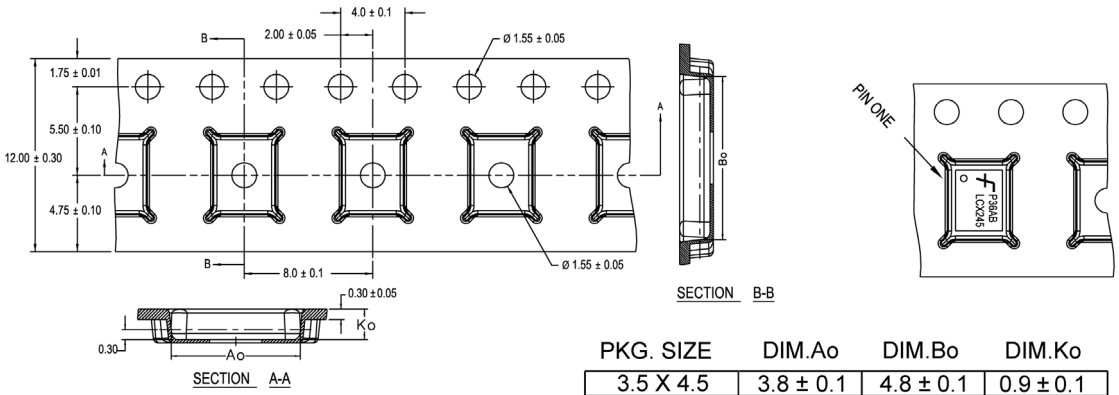
TAPE AND REEL SPECIFICATION

Tape Format for DQFN

TAPE FORMAT FOR DQFN

Package Designator	Tape Section	Number of Cavities	Cavity Status	Cover Tape Status
BQX	Leader (Start End)	125 (Typ.)	Empty	Sealed
	Carrier	3000	Filled	Sealed
	Trailer (Hub End)	75 (Typ.)	Empty	Sealed

Tape Dimensions (Inches (Millimeters))



PKG. SIZE	DIM.Ao	DIM.Bo	DIM.Ko
3.5 X 4.5	3.8 ± 0.1	4.8 ± 0.1	0.9 ± 0.1
3.0 X 3.0	3.3 ± 0.1	3.3 ± 0.1	0.9 ± 0.1
2.5 X 4.5	2.8 ± 0.1	4.8 ± 0.1	0.9 ± 0.1
2.5 X 3.5	2.8 ± 0.1	3.8 ± 0.1	0.9 ± 0.1
2.5 X 3.0	2.8 ± 0.1	3.3 ± 0.1	0.9 ± 0.1
2.5 X 2.5	2.8 ± 0.1	2.8 ± 0.1	0.9 ± 0.1

DIMENSIONS ARE IN MILLIMETERS

NOTES: unless otherwise specified

1. Cummulative pitch for feeding holes and cavities (chip pockets) not to exceed 0.008[0.20] over 10 pitch span.
2. Smallest allowable bending radius.
3. Thru hole inside cavity is centered within cavity.
4. Tolerance is ±0.002[0.05] for these dimensions on all 12mm tapes.
5. Ao and Bo measured on a plane 0.120[0.30] above the bottom of the pocket.
6. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
7. Pocket position relative to sprocket hole measured as true position of pocket. Not pocket hole.
8. Controlling dimension is millimeter. Diemension in inches rounded.

Figure 7. Tape Dimensions (Inches (Millimeters))

Reel Dimensions (Inches (Millimeters))

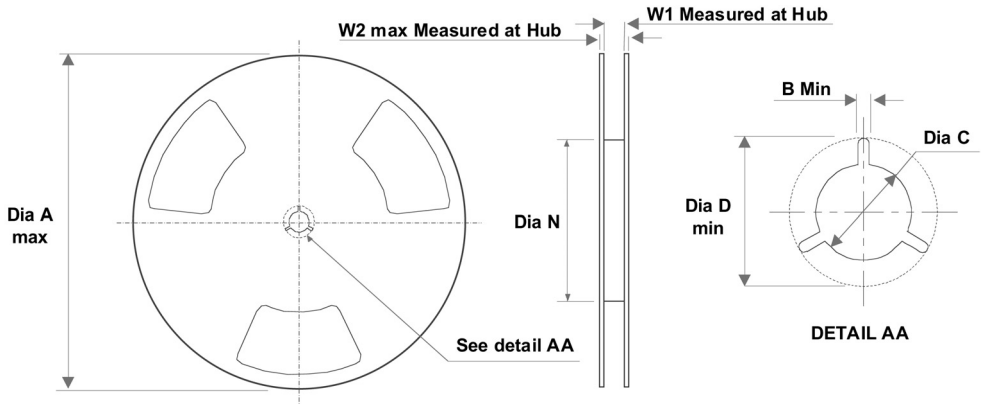


Figure 8.

Tape Size	A	B	C	D	N	W1	W2
12 mm	13.0 (330.0)	0.059 (1.50)	0.512 (13.00)	0.795 (20.20)	2.165 (55.00)	0.488 (12.4)	0.724 (18.4)

ORDERING INFORMATION

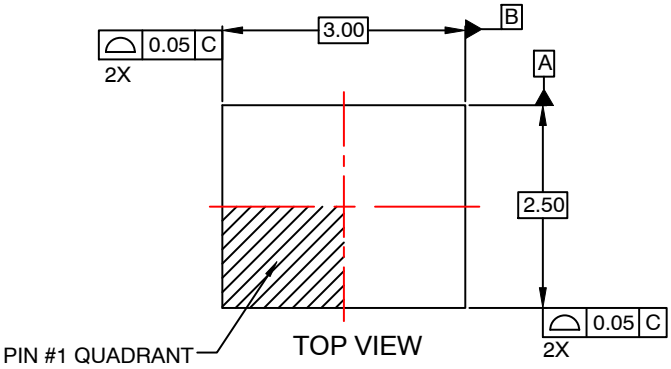
Ordering Number	Package Number	Package Description	Shipping†
74LCX32M	SOIC14	14−Lead Small Outline Integrated Circuit (SOIC), JEDEC MS−012, 0.150” Narrow	1100 Units / Tube
74LCX32BQX (Note 5)	QFN14	14−Terminal Depopulated Quad Very−Thin Flat Pack No Leads (DQFN), JEDEC MO−241, 2.5 x 3.0 mm	3000 Units / Tape & Reel
74LCX32MTC	TSSOP−14 WB	14−Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO−153, 4.4 mm Wide	2350 Units / Tube
74LCX32MTCX	TSSOP−14 WB	14−Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO−153, 4.4 mm Wide	2500 Units / Tape & Reel

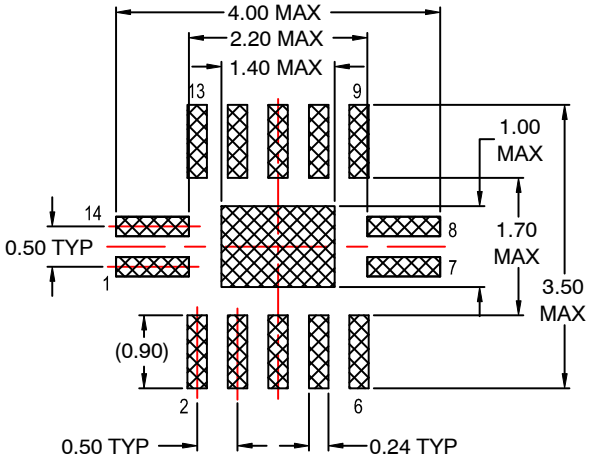
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

5. DQFN package available in Tape and Reel only.
6. Device also available in Tape and Reel. Specify by appending suffix letter “X” to the ordering number.
7. All packages are lead free per JEDEC: J−STD−020B standard.

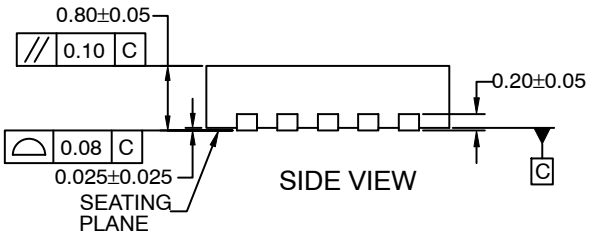
QFN14 3.0x2.5, 0.5P
CASE 510CB
ISSUE O

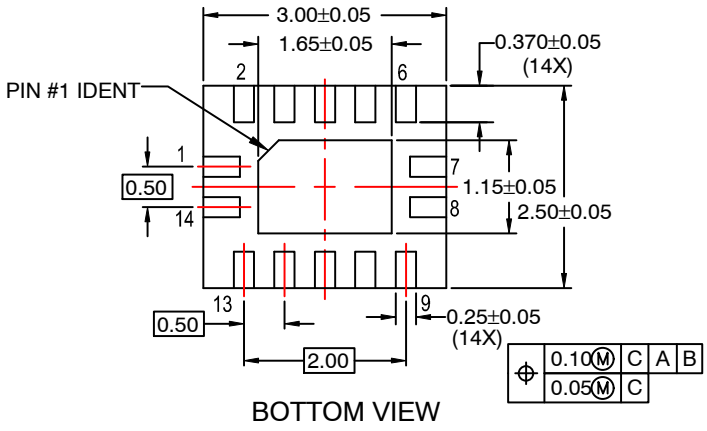
DATE 31 AUG 2016





RECOMMENDED LAND PATTERN





NOTES:

A. CONFORMS TO JEDEC REGISTRATION MO−241, VARIATION AA

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

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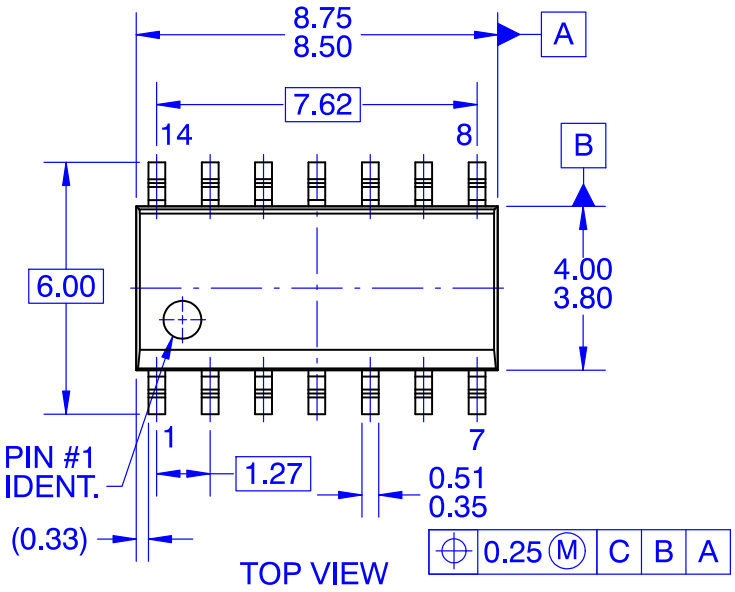
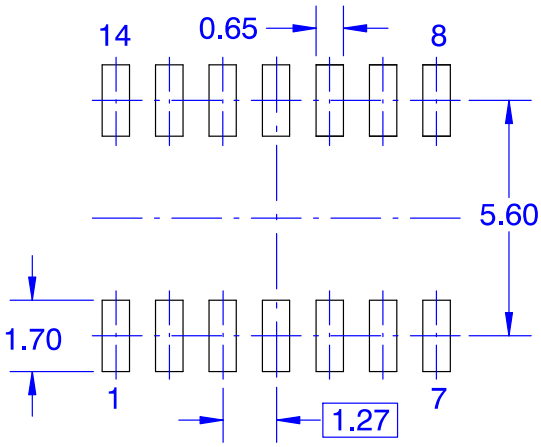
DESCRIPTION:	**QFN14 3.0X2.5, 0.5P**	**PAGE 1 OF 1**

SOIC14
CASE 751EF
ISSUE O

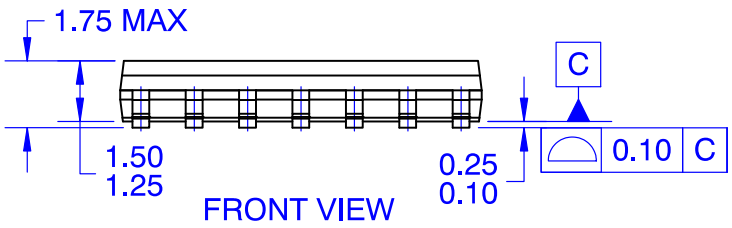
DATE 30 SEP 2016



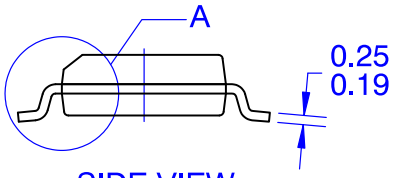
TOP VIEW



LAND PATTERN RECOMMENDATION

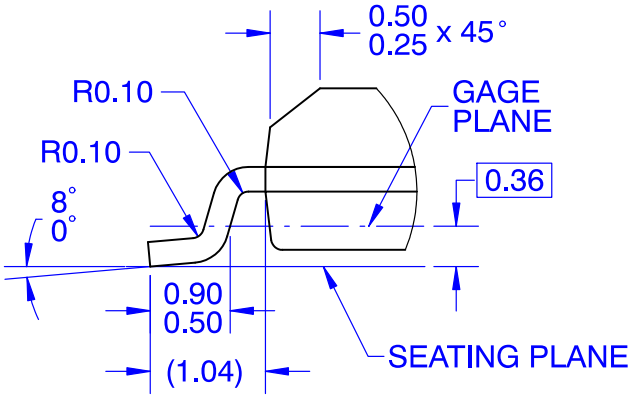


FRONT VIEW



SIDE VIEW

NOTES:
A. CONFORMS TO JEDEC MS−012, VARIATION AB, ISSUE C
B. ALL DIMENSIONS ARE IN MILLIMETERS
C. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS
D. LAND PATTERN STANDARD: SOIC127P600X145−14M
E. CONFORMS TO ASME Y14.5M, 2009



DETAIL A
SCALE 16 : 1

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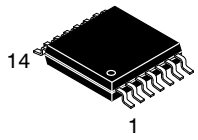
DESCRIPTION:	**SOIC14**	**PAGE 1 OF 1**

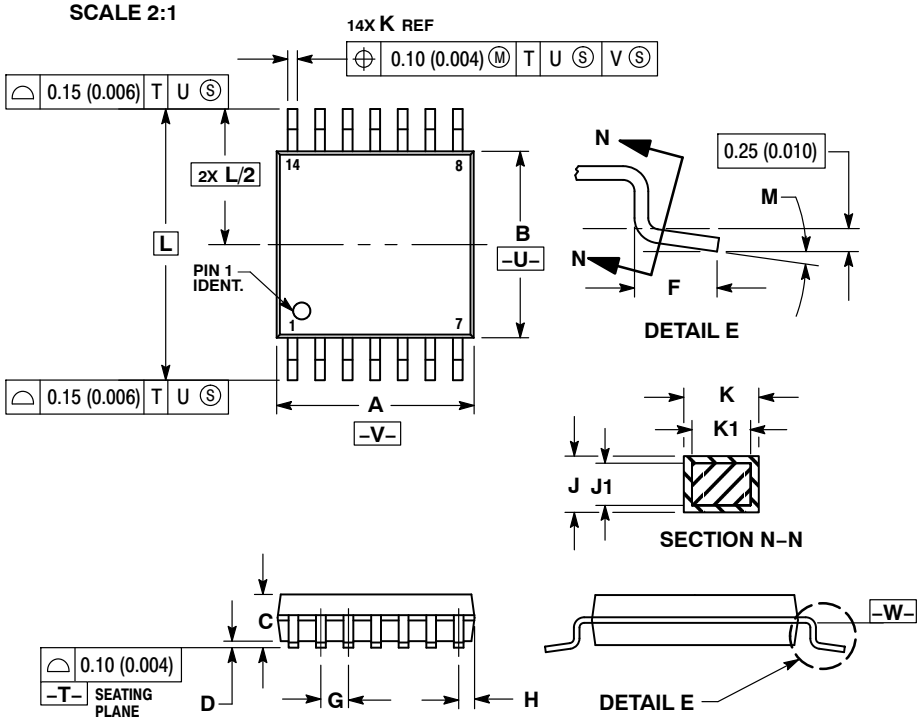
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

TSSOP−14 WB
CASE 948G
ISSUE C

DATE 17 FEB 2016



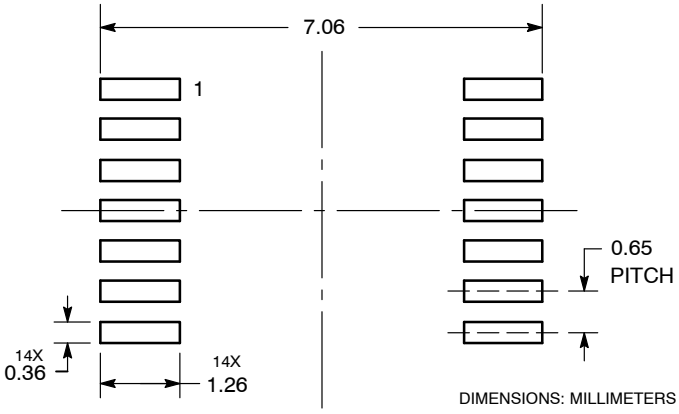
SCALE 2:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

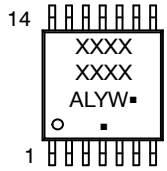
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**TSSOP−14 WB**	**PAGE 1 OF 1**

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